



micross®

one source. one solution.®

RECTIFIER, up to 600V, 3.4A, 50ns

3FF30

3FF40

3FF50

3FF60

2

AXIAL LEADED HERMETICALLY SEALED SUPERFAST RECTIFIER DIODE

QUICK REFERENCE DATA

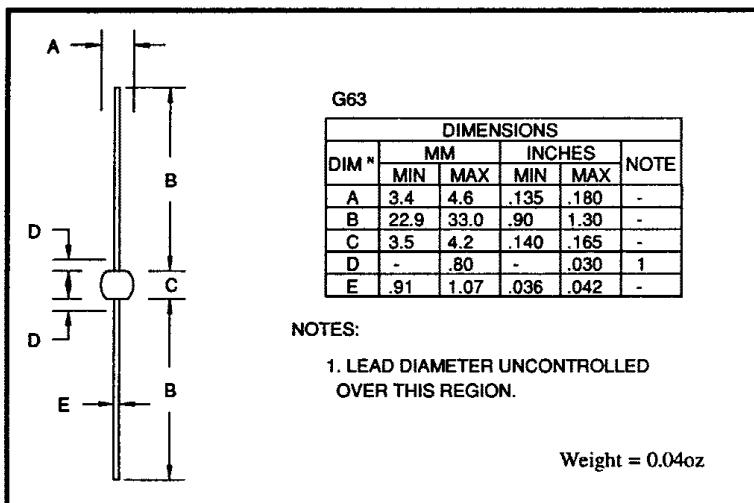
- Very low reverse recovery time
- Hermetically sealed with Metoxilite fused metal oxide
- Low switching losses
- Soft, non-snap off, recovery characteristics

- V_R = 300 - 600V
- I_F = 3.4A
- t_{rr} = 50ns
- I_R = 10 μ A

ABSOLUTE MAXIMUM RATINGS (@ 25°C unless otherwise specified)

	Symbol	3FF30	3FF40	3FF50	3FF60	Unit
Working reverse voltage	V_{RWM}	300	400	500	600	V
Repetitive reverse voltage	V_{RRM}	300	400	500	600	V
Average forward current (@ 55°C, lead length = 0.375")	$I_{F(AV)}$	3.4				A
Repetitive surge current (@ 55°C in free air, lead length 0.375")	I_{FRM}	15.0				A
Non-repetitive surge current ($t_p = 8.3\text{mS}$, @ V_R & T_{jmax})	I_{FSM}	70				A
Storage temperature range	T_{STG}	-65 to +150				°C
Operating temperature range	T_{OP}	-65 to +150				°C

MECHANICAL





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ELECTRICAL CHARACTERISTICS (@ 25°C unless otherwise specified)

	Symbol	3FF30	3FF40	3FF50	3FF60	Unit
Average forward current max. (pcb mounted; TA = 55°C) for sine wave for square wave (d = 0.5)	I _{F(AV)} I _{F(AV)}	1.0	1.1			A
Average forward current max. (T _L = 55°C; L = 3/8") for sine wave for square wave	I _{F(AV)} I _{F(AV)}	3.3	3.4			A
I ² t for fusing (t = 8.3mS) max.	I ² t	41				A ² S
Forward voltage drop max. @ I _F = 3.0A, T _j = 25°C	V _F	1.40				V
Reverse current max. @ VRWM, T _j = 25°C @ VRWM, T _j = 100°C	I _R I _R	10	500			µA
Reverse recovery time max. 0.5A I _F to 1.0A I _R . Recovers to 0.25A I _{RR} .	t _{rr}	50				nS
Junction capacitance typ. @ VR = 5V , f = 1MHz	C _j	125				pF

THERMAL CHARACTERISTICS

	Symbol	3FF30	3FF40	3FF50	3FF60	Unit
Thermal resistance - junction to lead Lead length = 0.375" Lead length = 0.0"	R _{θJL} R _{θJL}	20	5			°C/W
Thermal resistance - junction to amb. on 0.06" thick pcb. 1 oz. copper.	R _{θJA}	75				°C/W



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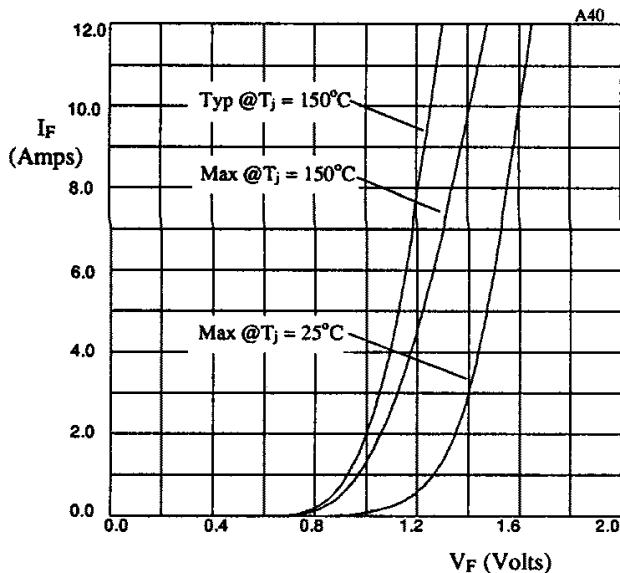


Fig 1. Forward voltage drops as a function of forward current

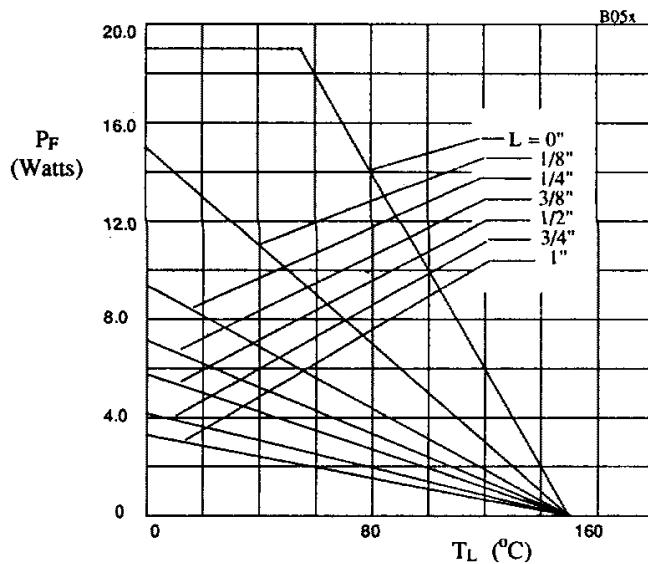


Fig 2. Maximum power versus lead temperature

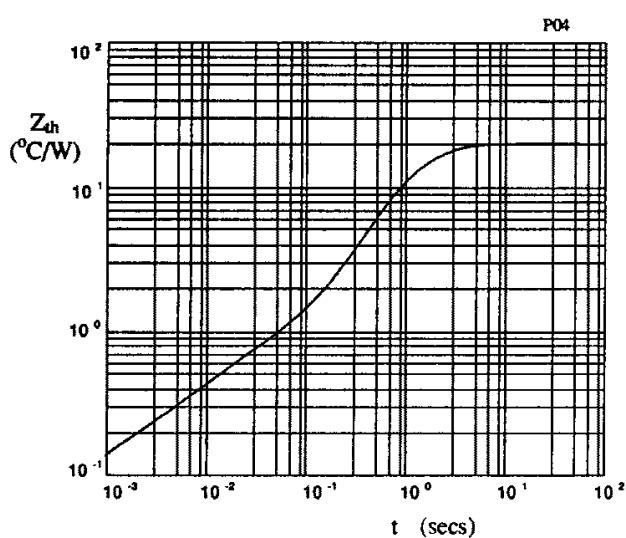


Fig 3. Transient thermal impedance characteristic.

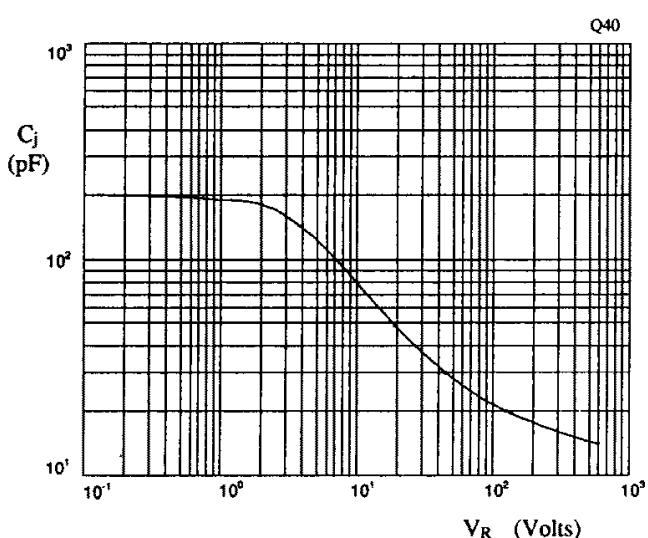


Fig 4. Typical junction capacitance as a function of reverse voltage.



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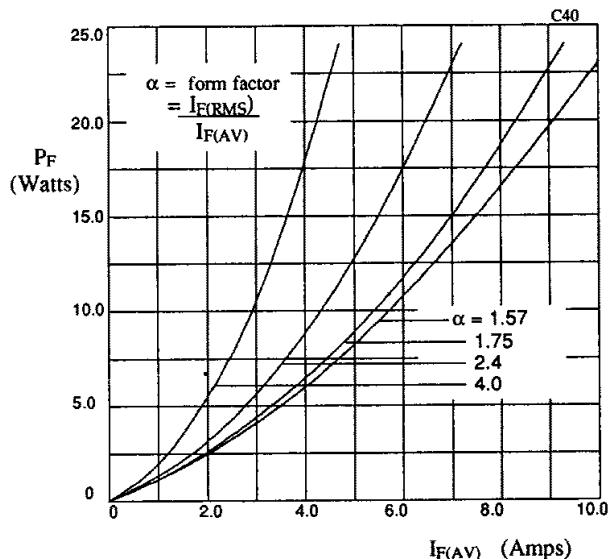


Fig 5. Forward power dissipation as a function of forward current, for sinusoidal operation.

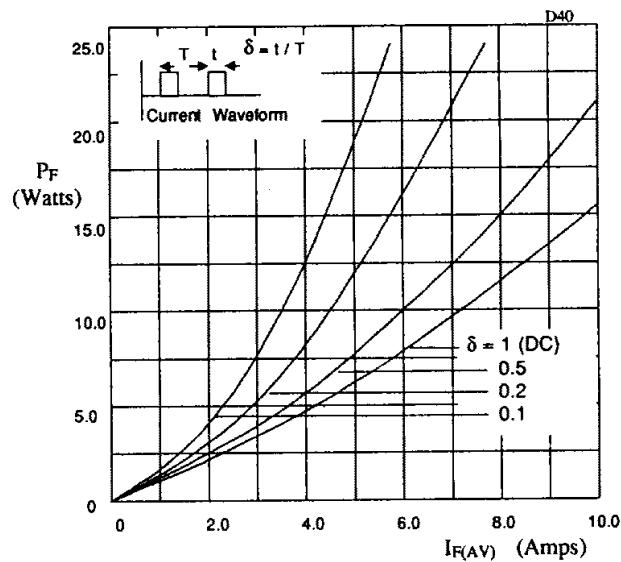


Fig 6. Forward power dissipation as a function of forward current, for square wave operation.

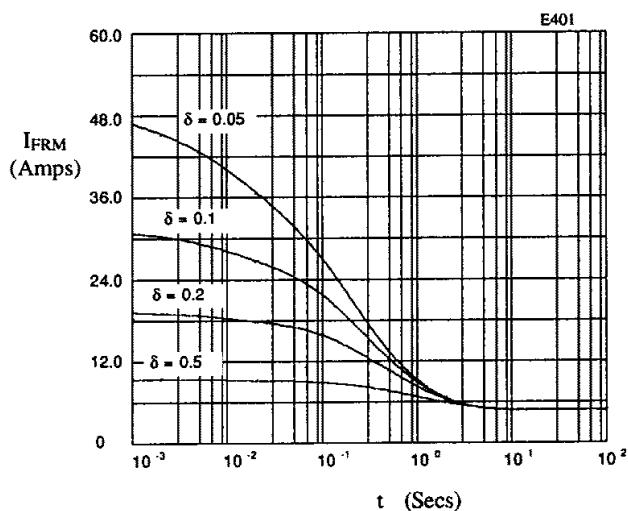


Fig 7. Typical repetitive forward current as a function of pulse width at 55°C; $R_{\theta JL} = 20 \text{ }^{\circ}\text{C/W}$; V_{RWM} during $1 - \delta$.

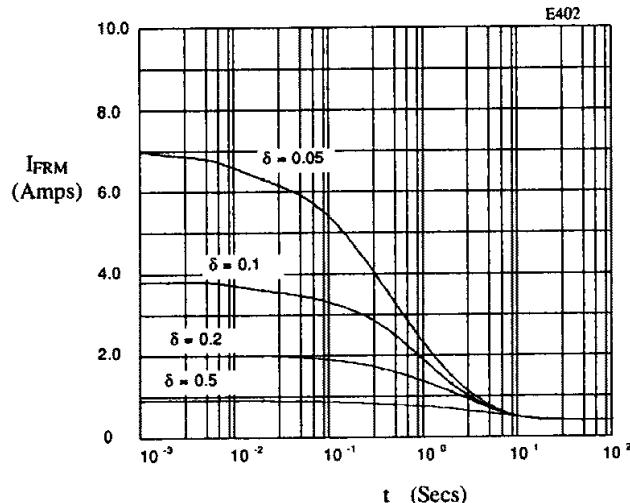


Fig 8. Typical repetitive forward current as a function of pulse width at 100°C; $R_{\theta JL} = 80 \text{ }^{\circ}\text{C/W}$; V_{RWM} during $1 - \delta$.